



Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No.	Application No.:
	UNTYP024	10/682,277
	Applicant:	
	Rinerson, et al.	
Filing Date	Group	
October 8, 2003	2818	

U.S. Patent Documents (Copies not supplied by Applicant)

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
TH	A	6,204,139	03/20/01	Liu, et al.	438	385	8/25/1998
	B	6,249,014	06/19/01	Bailey	257	295	10/1/1998
	C	6,566,753	05/20/03	Zhang, et al.	257	751	4/02/2002
TH	D	6,635,556	10/21/03	Herner, et al.	438	488	5/17/2001

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
	E	WO 0049659	24 Aug '00	PCT	H011	27/115	N/A	

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
TH	F	Beck, A. et al., "Reproducible switching effect in thin oxide films for memory applications," Applied Physics Letters, Vol. 77, No. 1, 3 July 2000, 139-141.
	G	Liu, S.Q., et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films", Applied Physics Letters, Vol. 76, No. 19, 8 May 2000, 2749-2651.
	H	Liu, S.Q., et al., "A New Concept For Non-Volatile Memory: Electric-Pulse Induced Reversible Resistance Change Effect In Magnetoresistive Films", Space Vacuum Epitaxy Center, University of Huston, Huston TX, 7 Pages.
	I	Park, In Seon et al., "Ultra-thin EBL (encapsulated barrier layer) for Ferroelectric Capacitor," IDEM, Vol 97, 617- 620.
	J	Rossel, C. et al., "Electrical current distribution across a metal-insulator-metal structure during bistable switching," Journal of Applied Physics, Vol. 90, No. 6, 15 September 2001, 2892-2898.
	K	Song, Yoon-Jong, "Ferroelectric Thin Films for High Density Non-volatile Memories," Virginia Polytechnic Institute and State University, August 13, 1998, Blacksburg, VA.
	L	Vijay, D.P. et al., "Electrodes for PbZr _x Ti _{1-x} O ₃ Ferroelectric Films," J. Electrochem. Soc., Vol. 140, No. 9, 4 September 1993, 2640-2645.
	M	Watanabe, Y. et al., "Current-driven insulator-conductor transition and nonvolatile memory in chromium-doped SrTiO ₃ single crystals," Applied Physics Letters, Vol. 78, No. 23, 4 June 2001, 3738-3740.
TH	N	Yoon, Dong-Soon et al., "High Performance of Novel Oxygen Diffusion Barrier Materials for Future High-Density Dynamic Random Access Memory Devices," IEEE Transactions on Electron Devices, Vol 49, No 11, November 2002, 1917-1927.
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		Date Considered

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.